

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of)
Hiroyuki UMIMOTO et al.)
Based On Application No. 09/996,932) Attn: Applications
Which Was Filed: November 30, 2001) Branch
For: SEMICONDUCTOR DEVICE)
AND METHOD OF FABRICATING)
THE SAME) Date: November 17, 2003

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

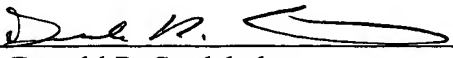
Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/996,932 filed November 30, 2001, and its predecessor Application No. 09/570,391, from which priority is claimed under 35 U.S.C. 120.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By: 
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known			
				Application Number		New Divisional Application	
				Filing Date		November 17, 2003	
				First Named Inventor		Hiroyuki UMIMOTO et al.	
				Art Unit		2825	
Examiner Name		Belur V. Keshavan					
Attorney Docket Number		740819-1039					
Sheet	1	of	1				

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-5,244,823	09-14-1993	Adan	
		US-5,320,974	06-14-1994	Hori et al.	
		US-5,401,994	03-28-1995	Adan	
		US-5,895,954	04-20-1999	Yasumura et al.	
		US-6,081,007	06-27-2000	Matsuoka	
		US-6,180,443	01-30-2001	Kang et al.	
		US-6,251,718	06-26-2001	Akamatsu et al.	
		US-6,306,712	10-23-2001	Rodder et al.	
		US-6,312,981	11-06-2001	Akamatsu et al.	
		US-6,479,356	11-12-2002	Matsuoka	
		US-6,579,770	06-17-2003	Rodder et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 11261069	09-24-1999	Rodder et al.		
		WO 97/50115	12-31-1997	Akamatsu et al.		
		JP 04158529 A	06-01-1992	Tanaka		
		JP 2000299447 A	10-24-2000	Oyu et al.		
		JP 2000049344 A	02-18-2000	Matsuoka		
		JP 10270687 A	10-09-1998	Yasumura et al.		
		JP 10294454 A	11-04-1998	Tanabe		
		JP 10065149 A	03-06-1998	Furukawa		
		JP 07022619 A	01-24-1995	Suzuki		
		JP 04343437 A	11-30-1992	Aruberuto		
		JP 08306923 A	11-22-1996	Yong-Taek		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		Shahidi et al. (October 1993) IEEE Electronics Device Letters, High-Performance Devices for a 0.15μm CMOS Technology , Vol. 14 No. 10 (pp.466-468).
		Bouillon et al. (1997) IEEE, Anomalous short channel effects in Indium implemented nMOSFETs , 4 pages.

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.